

General Description

The AGM635E combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

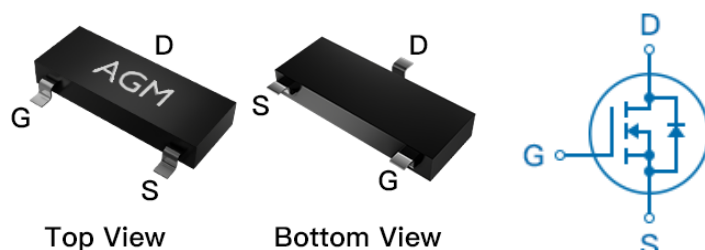
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
60V	32mΩ	5A

SOT23-3 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
635	AGM635E	SOT23-3	178mm	8mm	3000

Table 1. Absolute Maximum Ratings (TA=25 °C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	60	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Ta=25 °C) (Note 1)	5.0	A
	Drain Current-Continuous(Ta=70 °C)	2.9	A
IDM (pluse)	Drain Current-Pulsed (Note 2)	20	A
PD	Maximum Power Dissipation(Ta=25 °C)	1.2	W
TJ, TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State)1	---	104	°C/W

Table 3. Electrical Characteristics (TJ=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain- Source Breakdown Voltage	VGS=0V ID=250μA	60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=60V,VGS=0V	--	--	1	μA
IGSS	Gate- Body Leakage Current	VGS=±20V,VDS=0V	--	--	± 100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1.2	1.5	2.1	V
gFS	Forward Transconductance	VDS=5V,ID=4A	--	8	--	S
RDS(on)	Drain- Source On- State Resistance	VGS=10V, ID=5A	--	30	45	mΩ
		VGS=4.5V, ID=4A	--	38	52	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=20V,VGS=0V, F=1MHZ	--	980	--	PF
Coss	Output Capacitance		--	58	--	PF
Crss	Reverse Transfer Capacitance		--	49	--	PF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=20V RGEN=3Ω ,ID=5A	--	7.6	--	nS
tr	Turn-on Rise Time		--	20	--	nS
td(off)	Turn-Off Delay Time		--	3.7	--	nS
tf	Turn-Off Fall Time		--	5.3	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=20V, ID=5A	--	20	--	nC
Qgs	Gate- Source Charge		--	7.6	--	nC
Qgd	Gate- Drain Charge		--	15	--	nC
Source- Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	5.0	A
VSD	Forward on Voltage	VGS=0V,IS=5A	--	--	1.2	V
trr	Reverse Recovery Time	IF=5A , dI/dt=100A/μs ,	--	--	--	ns
Qrr	Reverse Recovery Charge	TJ= 2 5 °C	--	--	--	nc

Notes 1. The maximum current rating is package limited.

Notes 2. Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3. EAS condition: TJ=25℃

Test Circuit

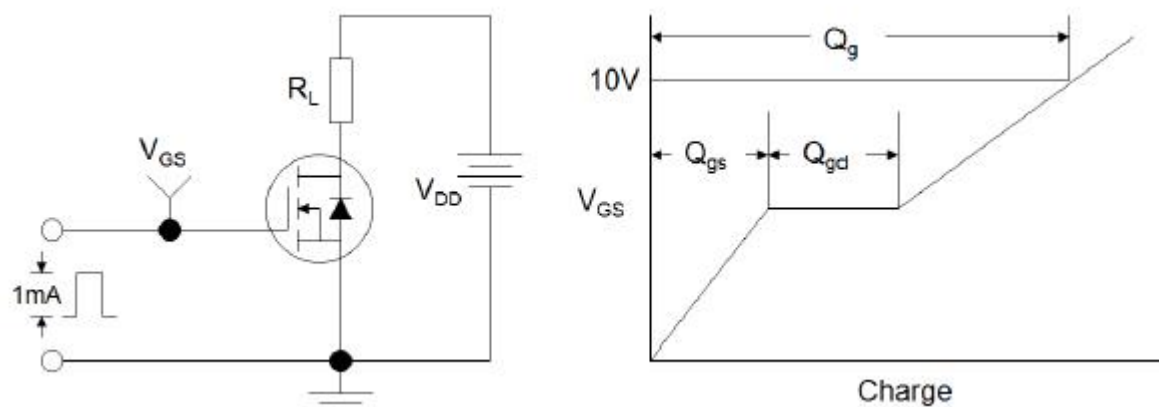


Figure1:Gate Charge Test Circuit & Waveform

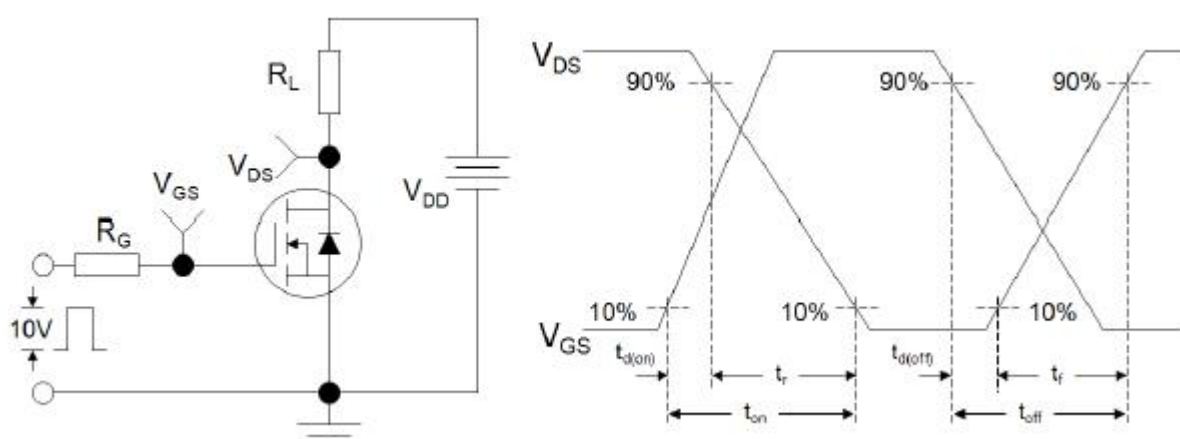


Figure 2: Resistive Switching Test Circuit & Waveforms

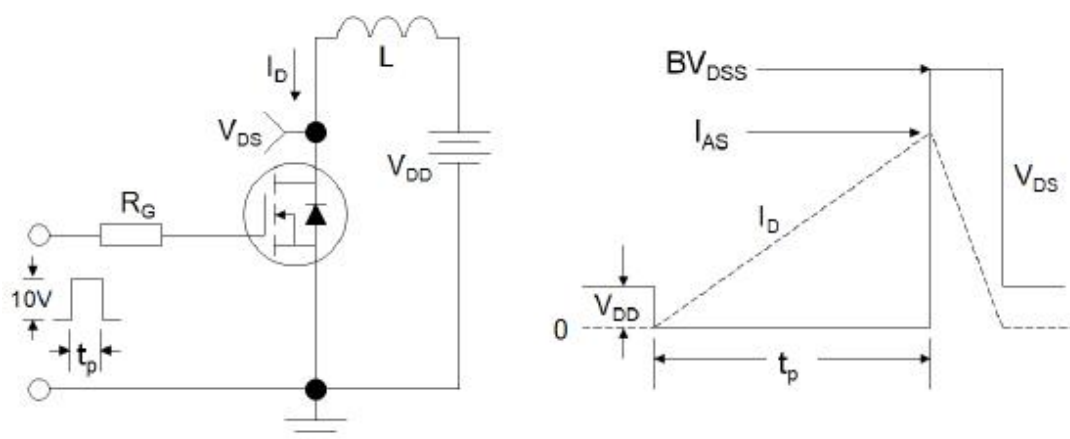
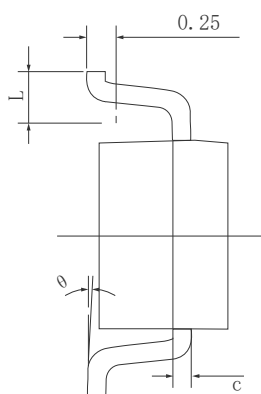
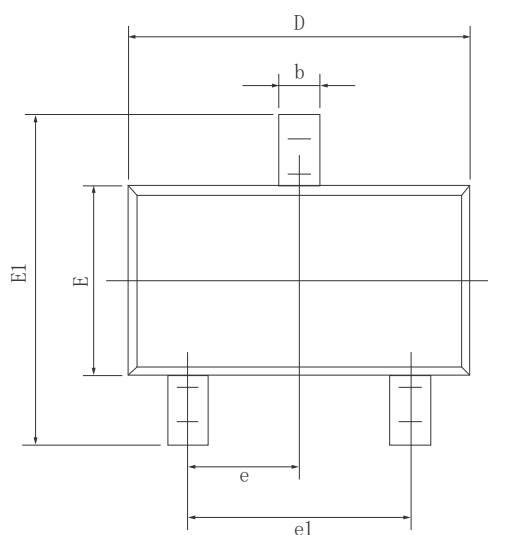
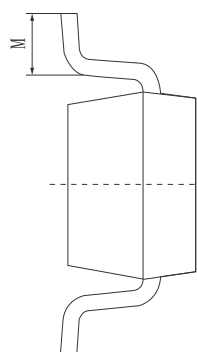
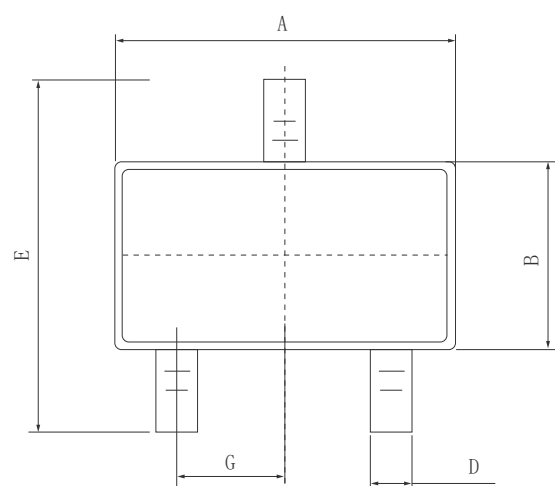
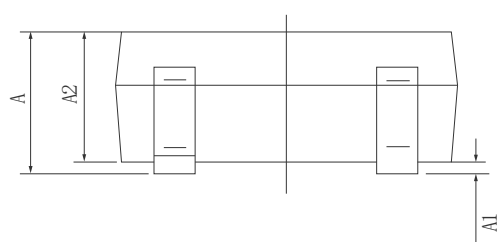


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms

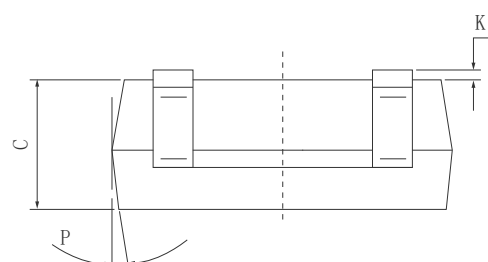
Dimensions (SOT23-3)



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	—	—	1.25
A1	0.03	—	0.10
A2	1.05	1.10	1.15
b	0.30	0.35	0.40
c	0.13	—	0.17
D	2.87	2.92	2.97
E	1.55	1.60	1.65
E1	2.70	2.85	3.00
e	0.95 BSC.		
e1	1.80	—	2.00
L	0.35	0.45	0.55
θ	0°	—	8°

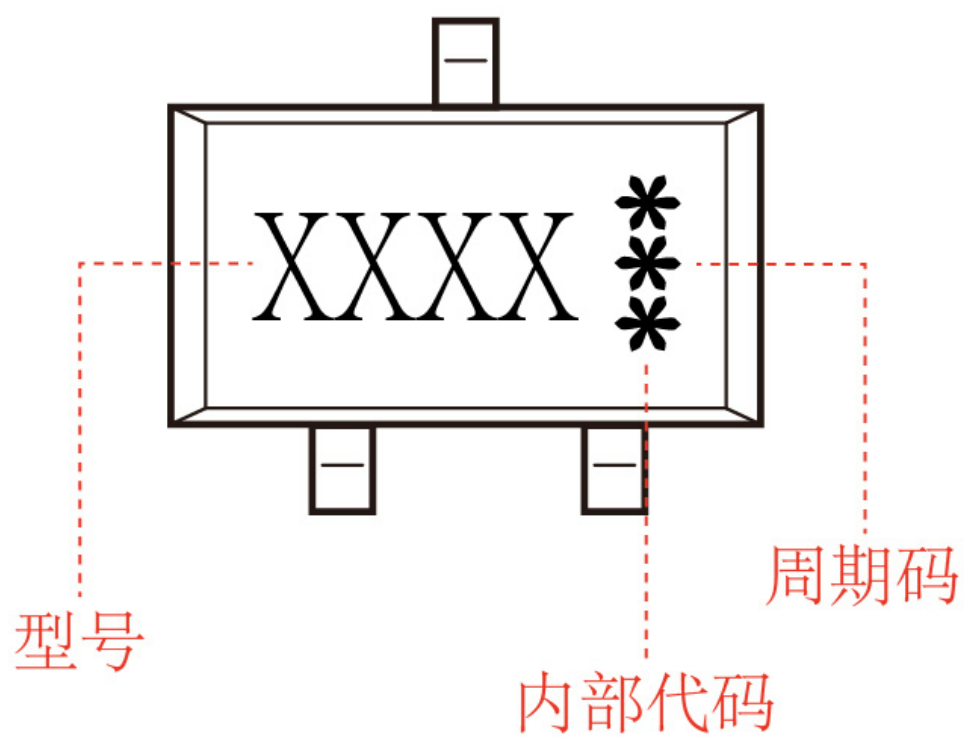


DIM	MILLIMETERS
A	2.82~3.02
B	1.60±0.10
C	1.10±0.05
D	0.40±0.10
E	2.65~2.95
G	0.95typ
K	0.00~0.10
M	0.20MIN
P	9±2°



SOT23-3

Marking Instructions:



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